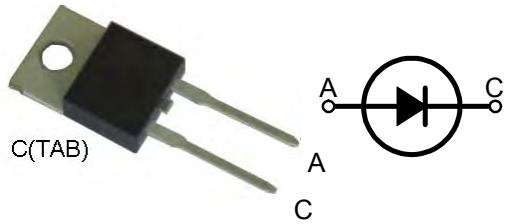
MBR730 thru MBR745

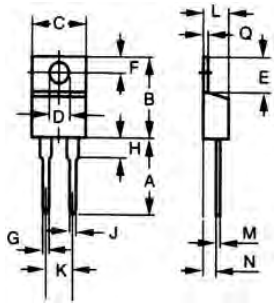
High Tjm Low IRRM Schottky Barrier Diodes



A=Anode, C=Cathode, TAB=Cathode

	V_{RRM}	V_{RMS}	V_{DC}
	V	V	V
MBR730	30	21	30
MBR735	35	24.5	35
MBR740	40	28	40
MBR745	45	31.5	45

Dimensions TO-220AC



Dim.	Inches		Milimeter	
	Min.	Max.	Min.	Max.
A	0.500	0.580	12.70	14.73
B	0.560	0.650	14.23	16.51
C	0.380	0.420	9.66	10.66
D	0.139	0.161	3.54	4.08
E	2.300	0.420	5.85	6.85
F	0.100	0.135	2.54	3.42
G	0.045	0.070	1.15	1.77
H	-	0.250	-	6.35
J	0.025	0.035	0.64	0.89
K	0.190	0.210	4.83	5.33
L	0.140	0.190	3.56	4.82
M	0.015	0.022	0.38	0.56
N	0.080	0.115	2.04	2.49
Q	0.025	0.055	0.64	1.39

Symbol	Characteristics	Maximum Ratings	Unit
$I_{(AV)}$	Maximum Average Forward Rectified Current @T_C=125°C	7.5	A
I_{FSM}	Peak Forward Surge Current 8.3ms Single Half-Sine-Wave Superimposed On Rated Load (JEDEC METHOD)	150	A
dv/dt	Voltage Rate Of Change (Rated V_R)	10000	V/us
V_F	Maximum Forward Voltage (Note 1) I_F=7.5A @T_J=25°C I_F=7.5A @T_J=125°C I_F=15A @T_J=25°C I_F=15A @T_J=125°C	- 0.57 0.84 0.72	V
I_R	Maximum DC Reverse Current @T_J=25°C At Rated DC Blocking Voltage @T_J=125°C	0.1 15	mA
$R_{\Theta JC}$	Typical Thermal Resistance (Note 2)	3.5	°C/W
C_J	Typical Junction Capacitance (Note 3)	400	pF
T_J	Operating Temperature Range	-55 to +150	°C
T_{STG}	Storage Temperature Range	-55 to +175	°C

NOTES: 1. 300us Pulse Width, Duty Cycle 2%.
2. Thermal Resistance Junction To Case.
3. Measured At 1.0MHz And Applied Reverse Voltage Of 4.0V DC.

FEATURES

* Metal of silicon rectifier, majority carrier conducton
* Guard ring for transient protection
* Low power loss, high efficiency
* High current capability, low V_F
* High surge capacity
* For use in low voltage, high frequency inverters, free whelling, and polarity protection applications
* RoHS compliant

MECHANICAL DATA

* Case: TO-220AC molded plastic
* Polarity: As marked on the body
* Weight: 2 grams
* Mounting position: Any

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MBR730 thru MBR745

High Tjm low IRRM Schottky Barrier Diodes

FIG.1 - FORWARD CURRENT DERATING CURVE

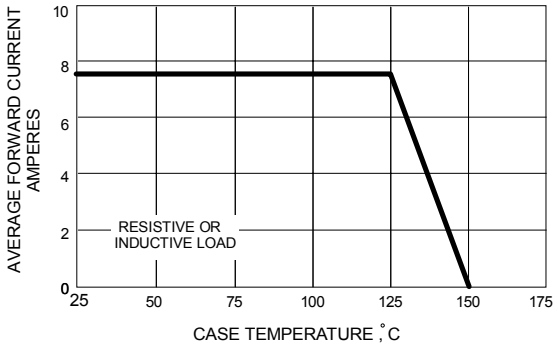


FIG.2 - MAXIMUM NON-REPETITIVE SURGE CURRENT

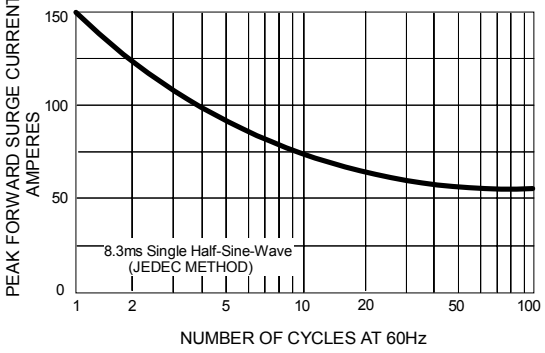


FIG.3 - TYPICAL REVERSE CHARACTERISTICS

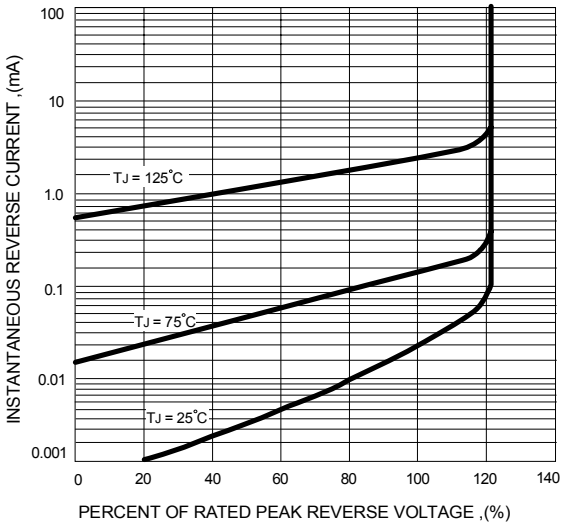


FIG.4 - TYPICAL FORWARD CHARACTERISTICS

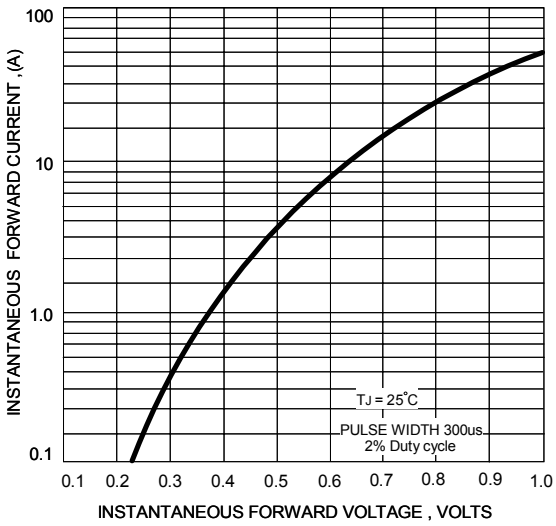
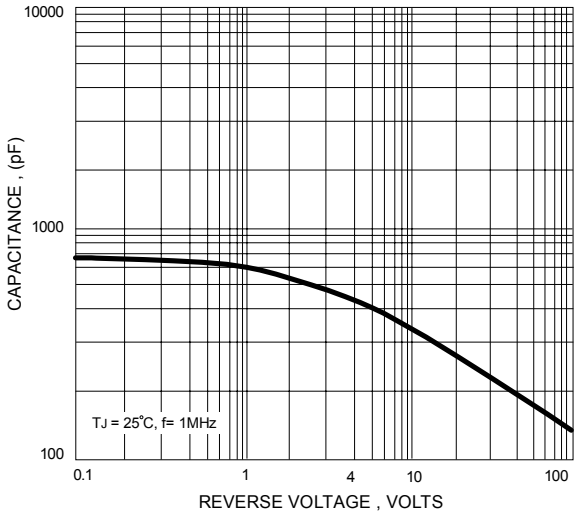


FIG.5 - TYPICAL JUNCTION CAPACITANCE



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